# Hiroshi Fukuda

List of Publications by Year
in descending order

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| 28 | 457 | 840776<br>11 | 888059<br>17 |
|---|---|---|---|
| papers | citations | h-index | g-index |

| 28 | 28 | 28 | 172 |
|---|---|---|---|
| all docs | docs citations | times ranked | citing authors |

| # | Article | IF | Citations |
|---|---|---|---|
| 1 | Imaging Characteristics of Multi-Phase-Shifting and Halftone Phase-Shifting Masks. Japanese Journal of Applied Physics, 1991, 30, 2991-2997. | 1.5 | 80 |
| 2 | Characterization of line-edge roughness in resist patterns and estimations of its effect on device performance. , 2003, 5038, 689. | | 45 |
| 3 | Spectral analysis of line-edge roughness in polyphenol EB-resists and its impact on transistor performance. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2005, 23, 2711. | 1.6 | 43 |
| 4 | Analysis of Line Edge Roughness Using Probability Process Model for Chemically Amplified Resists. Japanese Journal of Applied Physics, 2003, 42, 3748-3754. | 1.5 | 39 |
| 5 | Depth Profile and Line-Edge Roughness of Low-Molecular-Weight Amorphous Electron Beam Resists. Japanese Journal of Applied Physics, 2005, 44, 5484-5488. | 1.5 | 36 |
| 6 | Metrology of LER: influence of line-edge roughness (LER) on transistor performance. , 2004, , . | | 32 |
| 7 | Impact of Long-Period Line-Edge Roughness (LER) on Accuracy in Critical Dimension (CD) Measurement and New Guideline for CD Metrology. Japanese Journal of Applied Physics, 2005, 44, 5575-5580. | 1.5 | 26 |
| 8 | Fabrication of silicon nanopillars containing polycrystalline silicon/insulator multilayer structures. Applied Physics Letters, 1997, 70, 333-335. | 3.3 | 23 |
| 9 | Analysis of Line-edge Roughness in Resist Patterns and Its Transferability as Origins of Device Performance Degradation and Variation. Journal of Photopolymer Science and Technology = [Fotoporima Konwakai Shi], 2003, 16, 387-393. | 0.3 | 22 |
| 10 | Depth profile and line-edge roughness of partiallyO-1-ethoxyethylated low molecular weight amorphous polyphenol and poly(p-hydroxystyrene) base resists for electron-beam lithography. Polymers for Advanced Technologies, 2006, 17, 116-121. | 3.2 | 19 |
| 11 | Evaluation of Pupil-Filtering in High-Numerical Aperture I-Line Lens. Japanese Journal of Applied Physics, 1993, 32, 5845-5849. | 1.5 | 13 |
| 12 | LER evaluation of molecular resist for EUV lithography. Microelectronic Engineering, 2007, 84, 1084-1087. | 2.4 | 12 |
| 13 | Molecular Resists Based on Cholate Derivatives for Electron-Beam Lithography. Japanese Journal of Applied Physics, 2006, 45, 5435-5439. | 1.5 | 11 |
| 14 | Recording Density Limitation Explored by Head/Media Co-Optimization Using Genetic Algorithm and GPU-Accelerated LLG. IEEE Transactions on Magnetics, 2012, 48, 3895-3898. | 2.1 | 9 |
| 15 | Localized and cascading secondary electron generation as causes of stochastic defects in extreme ultraviolet projection lithography. Journal of Micro/ Nanolithography, MEMS, and MOEMS, 2019, 18, 1. | 0.9 | 9 |
| 16 | Molecular resists based on cholate derivatives for electron-beam lithography. , 2006, 6153, 762. | | 8 |
| 17 | Cascade and cluster of correlated reactions as causes of stochastic defects in extreme ultraviolet lithography. Journal of Micro/ Nanolithography, MEMS, and MOEMS, 2020, 19, 1. | 0.9 | 6 |
| 18 | Measurement of pattern roughness and local size variation using CD-SEM. Journal of Micro/ Nanolithography, MEMS, and MOEMS, 2018, 17, 1. | 0.9 | 5 |

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|---|---|---|---|
| 19 | Estimating extremely low probability of stochastic defect in extreme ultraviolet lithography from critical dimension distribution measurement. Journal of Micro/ Nanolithography, MEMS, and MOEMS, 2019, 18, 1. | 0.9 | 4 |
| 20 | Performance Limitation of Microwave Assisted Magnetic Recording Combined With Exchange Coupled Composite Media Explored by Genetic Algorithm. IEEE Transactions on Magnetics, 2013, 49, 3640-3643. | 2.1 | 3 |
| 21 | Measurement of pattern roughness and local size variation using CD-SEM: current status. , 2018, , . | | 3 |
| 22 | Impact of asymmetrically localized and cascading secondary electron generation on stochastic defects in EUV lithography. , 2019, , . | | 3 |
| 23 | <title>Effects of radially nonsymmetric pupil filters and multiple-pupil exposure</title>. , 1996, 2726, 375. | | 2 |
| 24 | Stochastic defect generation in EUV lithography analyzed by spatially correlated probability model, reaction-limited and scattering-limited?. , 2019, , . | | 2 |
| 25 | Dissolution nonlinearity tail degradation with decreased reaction events impacts EUV stochastic defect generations. , 2020, , . | | 2 |
| 26 | Auxiliary pattern generation to cancel unexpected images at sidelobe overlap regions in attenuated phase-shift masks. , 1999, , . | | 0 |
| 27 | Root-cause decomposition of line edge roughness and its application to cross-section profile prediction using top-view SEM images. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2013, 31, 06F802. | 1.2 | 0 |
| 28 | Cross-sectional profile prediction from top-view SEM images based on root-cause decomposition of line-edge roughness. Proceedings of SPIE, 2014, , . | 0.8 | 0 |